



# **Bi-Directional N-Channel 30-V (D-S) MOSFET**

PRODUCT SUMMARY				
V <sub>S1S2</sub> (V)	$R_{S1S2(on)}\left(\Omega\right)$	I <sub>S1S2</sub> (A)		
30	$0.045$ at $V_{GS} = 4.5 \text{ V}$	4.9		
	0.060 at V <sub>GS</sub> = 2.5 V	4.2		

### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- Ultra-Low  $R_{SS(on)}$  and 22.5  $m\Omega$  Maximum Effective On-Resistance

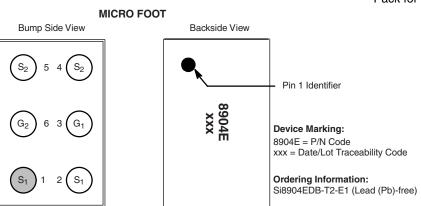


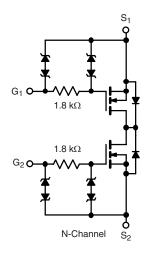
ROHS

- ESD Protected: 4000 V
- MICRO FOOT<sup>®</sup> Chipscale Packaging Reduces Footprint Area, Profile (0.65 mm) and On-Resistance Per Footprint Area

### **APPLICATIONS**

Battery Protection Circuit
-1-2 Cell Li+/LiP Battery
Pack for Portable Devices





<b>ABSOLUTE MAXIMUM RATINGS</b> T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter	Symbol	5 s	Steady State	Unit		
Source1- Source2 Voltage		$V_{S1S2}$	30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
Continuos Common Common /T 150 000	T <sub>A</sub> = 25 °C	l	4.9	3.8		
Continuous Source1- Source2 Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 85 °C	I <sub>S1S2</sub>	3.5	2.7	Α	
Pulsed Source1- Source2 Current		I <sub>SM</sub>	25			
Mariana Barra Birata di ad	T <sub>A</sub> = 25 °C	D.	P <sub>D</sub> 1.7 1		W	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 85 °C	L D	0.8	0.5	VV	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	
Package Reflow Conditions <sup>c</sup>	IR/Convection		260		C	

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Marrian una lungation de Ambriando	t ≤ 5 s	R <sub>thJA</sub>	60	75	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State	' ¹thJA	95	120	°C/W
Maximum Junction-to-Foot <sup>b</sup>	Steady State	$R_{thJF}$	18	22	

#### Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. The foot is defined as the top surface of the package.
- c. Refer to IPC/JEDEC (J-STD-020C), no manual or hand soldering.

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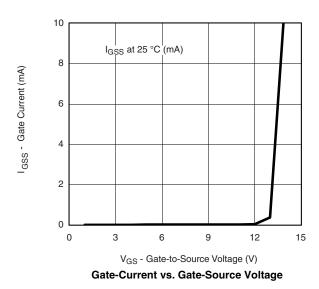
SPECIFICATIONS T <sub>J</sub> = 25 °C, unless otherwise noted							
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	$V_{GS(th)}$	$V_{SS} = V_{GS}, I_D = 250 \mu A$	0.6		1.6	>	
Cata Badul salara	lana	$V_{SS} = 0 \text{ V}, V_{GS} = \pm 4.5 \text{ V}$			± 4	μΑ	
Gate-Body Leakage	IGSS	$V_{SS} = 0 \text{ V}, V_{GS} = \pm 12 \text{ V}$			± 10	mA	
Zara Cata Valtaga Cauraa Current	1	V <sub>SS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	μΑ	
Zero Gate Voltage Source Current	I <sub>S1S2</sub>	$V_{SS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 85 ^{\circ}\text{C}$			5		
On-State Source Current <sup>a</sup>	I <sub>S(on)</sub>	$V_{SS} = 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	5			Α	
	В	V <sub>GS</sub> = 4.5 V, I <sub>SS</sub> = 1 A		0.037	0.045	0	
Source1- Source2 On-State Resistance <sup>a</sup>	a R <sub>S1S2(on)</sub>	V <sub>GS</sub> = 2.5 V, I <sub>SS</sub> = 1 A		0.048	0.060	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>SS</sub> = 10 V, I <sub>SS</sub> = 1 A		12		S	
Dynamic <sup>b</sup>							
Turn-On Delay Time	t <sub>d(on)</sub>			1.6	2.4		
Rise Time	t <sub>r</sub>	$V_{SS}$ = 10 V, $R_L$ = 10 $\Omega$		2	3		
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_{SS}\cong$ 1 A, $V_{GEN}$ = 4.5 V, $R_g$ = 6 $\Omega$		1.5	2.3	μs	
Fall Time	t <sub>f</sub>			3.7	5.6		

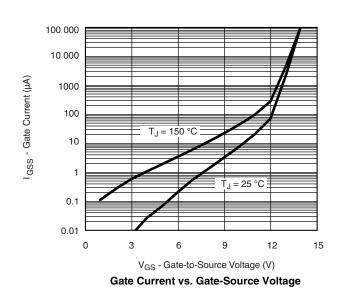
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



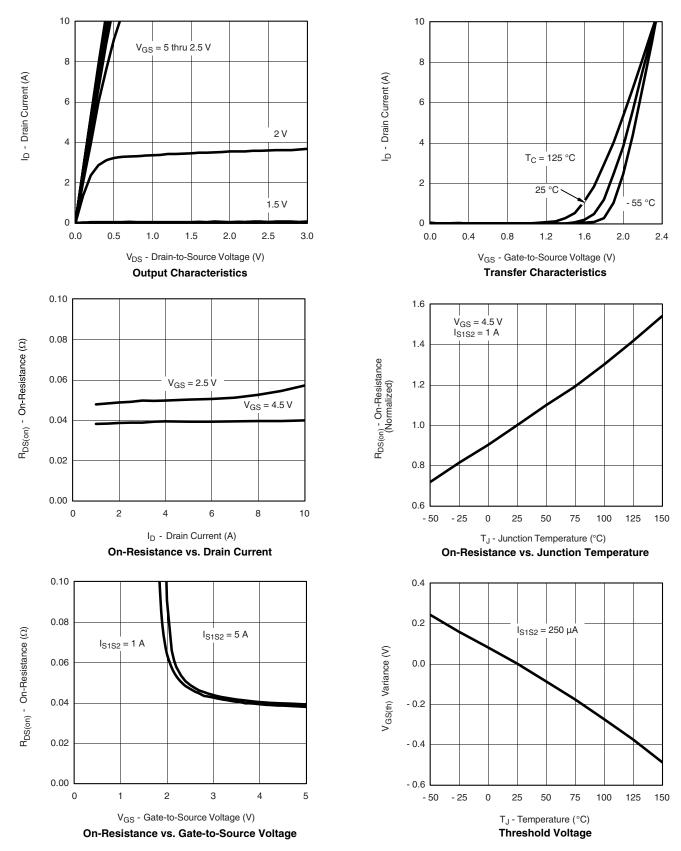








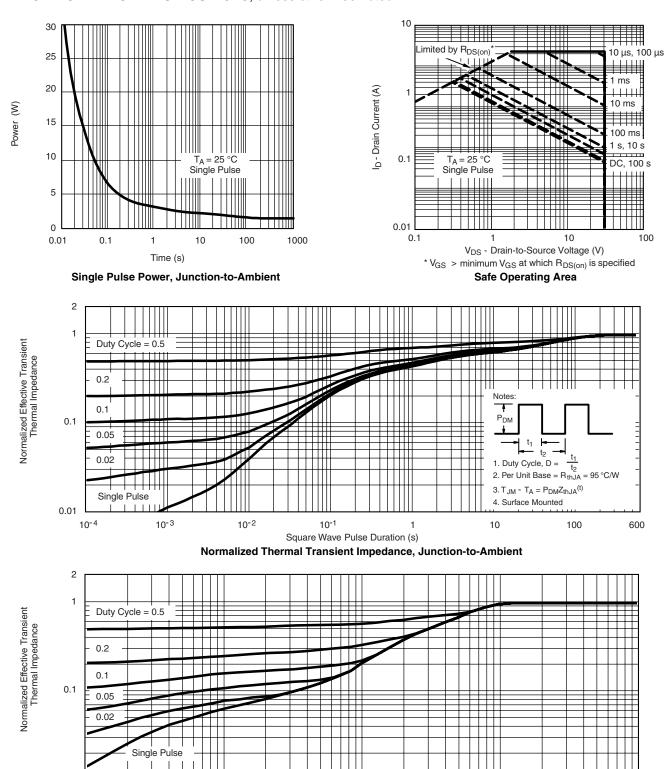
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Square Wave Pulse Duration (s)

10<sup>-2</sup>

10-3

0.01

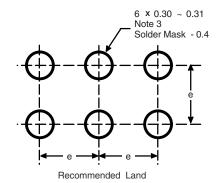
10-4

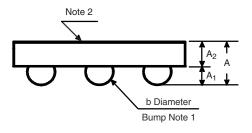
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## **PACKAGE OUTLINE**

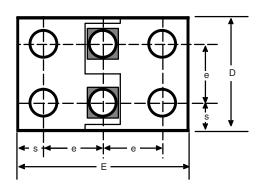
## MICRO FOOT: 6-BUMP (2 x 3, 0.8 mm PITCH)







Mark on Backside of Die



Notes (Unless Otherwise Specified):

- 1. 6 solder bumps are 95.5/3.8/0.7 Sn/Ag/Cu.
- 2. Backside surface is coated with a Ag/Ni/Ti layer.
- 3. Non-solder mask defined copper landing pad.
- 4. Laser marks on the silicon die back.

Dim.	Millim	eters <sup>a</sup>	Inches		
	Min.	Max.	Min.	Max.	
Α	0.600	0.650	0.0236	0.0256	
<b>A</b> <sub>1</sub>	0.260	0.290	0.102	0.114	
A <sub>2</sub>	0.340	0.360	0.0134	0.0142	
b	0.370	0.410	0.0146	0.0161	
D	1.520	1.600	0.0598	0.0630	
E	2.320	2.400	0.0913	0.0945	
е	0.750	0.850	0.0295	0.0335	
s	0.380	0.400	0.0150	0.0157	

#### Notes:

a. Use millimeters as the primary measurement.

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